Maplesemi

LEAD FREE RoHS

SLV3407T
-30V P -Channel MOSFET

General Description

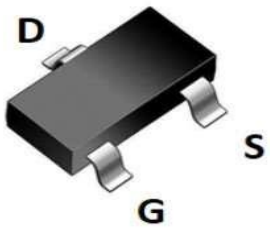
This Power MOSFET is produced using Maple semi's advanced planar stripeTRENCH technology.
This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

Features

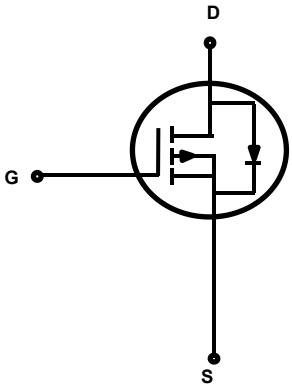
- P-Channel: -30V -4.1A
  $R_{DS(on)Typ}$= 36mΩ@V_{GS} = -10V
  $R_{DS(on)Typ}$=52mΩ@V_{GS} = -4.5V
- Very Low On-resistance RDS(ON)
- LowCrss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Application

- Battery Protection
- Load Switch
- Power Management



SOT-23



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter	SLV3407T	Units
V_{DSS}	Drain-Source Voltage	-30	V
I_D	Drain Current - Continuous (T_C = 25℃)	-4.1	A
	- Continuous (T_C = 70℃)	-3.2	A
I_{DM}	Drain Current - Pulsed (Note 1)	-15	A
V_{GSS}	Gate-Source Voltage	±20	V
P_D	Power Dissipation (T_A = 25℃)	1.2	W
	Power Dissipation (T_A =70℃)	0.8	
$R_{\theta JA}$	Thermal Resistance, Junction to Case	105	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	℃

* Drain current limited by maximum junction temperature.

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D =- 250 uA	-30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =-30 V, V_{GS} = 0 V	--	--	-1.0	uA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 20V, V_{DS} = 0 V	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -20 V, V_{DS} = 0 V	--	--	100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 uA	-1	-1.5	-2.4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} =-10 V, I_D =- 4.1A	--	36	49	mΩ
		V_{GS} =-4.5V, I_D = -3.5A	--	52	65	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -15 V, V_{GS} = 0 V, f = 1.0 MHz	--	572	-	pF
C_{oss}	Output Capacitance		--	82	-	pF
C_{rss}	Reverse Transfer Capacitance		--	70	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{GS}=-10V, V_{DS}=-15 V, R_G = 2.5Ω ,R_L=15Ω	--	3.8	--	ns
t_r	Turn-On Rise Time		--	17.6	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	17.8	--	ns
t_f	Turn-Off Fall Time		--	21.8	--	ns
Q_g	Total Gate Charge	V_{DS} = -15 V, I_D =-4.1A, V_{GS} = -10V	--	11.65	--	nC
Q_{gs}	Gate-Source Charge		--	2.32	--	nC
Q_{gd}	Gate-Drain Charge		--	2.08	--	nC
Qrr	Reverse Recovery Chrage	I_F =-10A, di/dt=100A/us		0.643		nC
t_{rr}	Reverse Recovery Time	I_F =-10A, di/dt=100A/us		15.7		ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	-4.1	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-16	A
V_{SD}	Drain to Source Diode Forward Voltage,V GS = 0V, I_{SD} =-4.1A,T J = 25°C		--	--	-1.2	V

Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

P- Channel Typical Characteristics

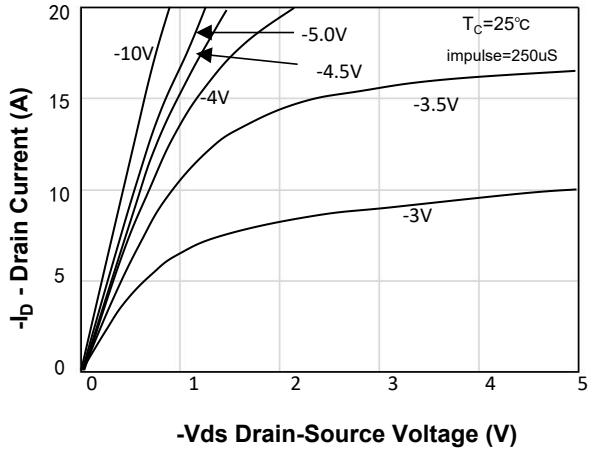


Figure 1. On-Region Characteristics

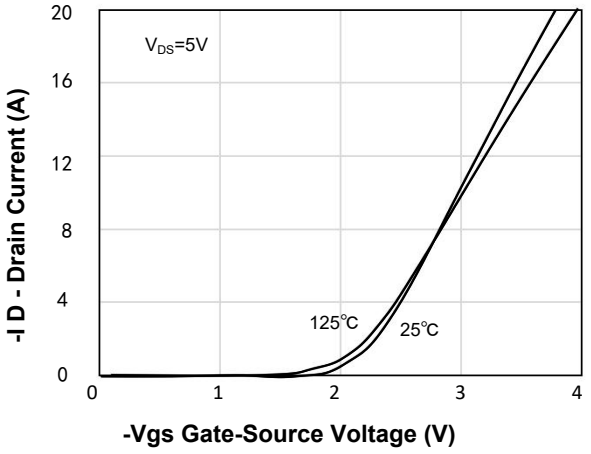


Figure 2. Transfer Characteristics

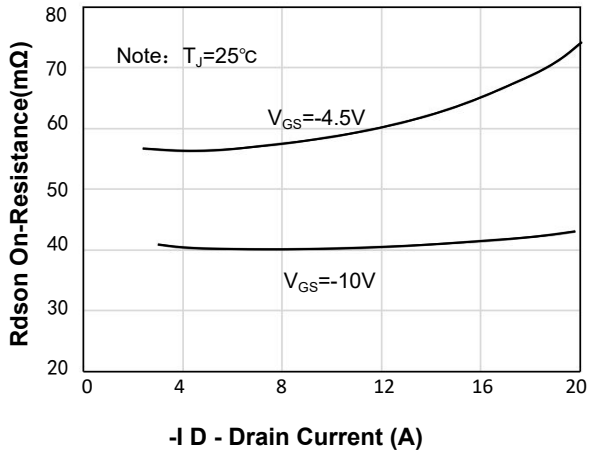


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

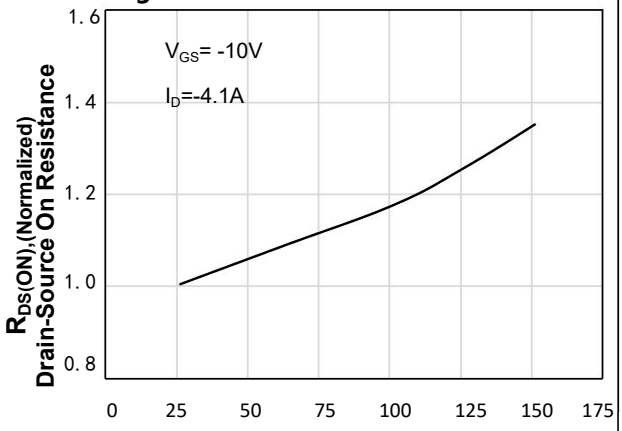


Figure 4. On-Resistance Variation vs Temperature

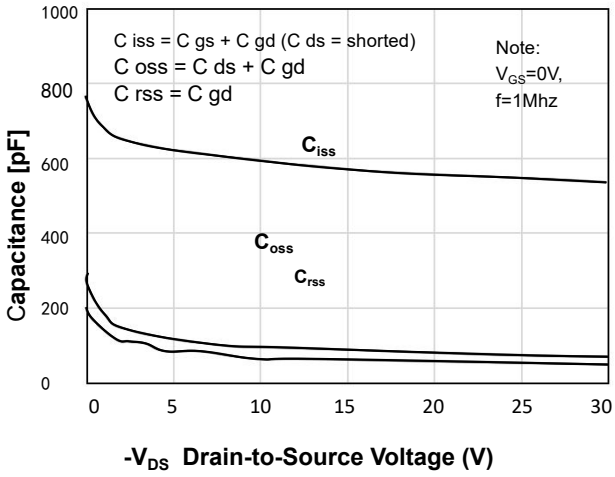


Figure 5. Capacitance Characteristics

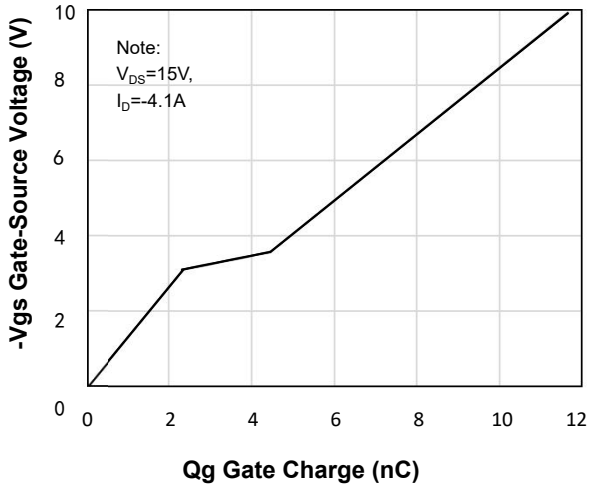


Figure 6. Gate Charge Characteristics

P- Channel Typical Characteristics (Continued)

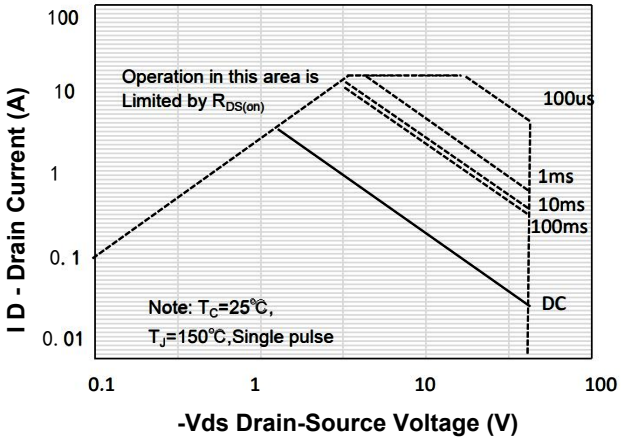


Figure 7. Maximum Safe Operating Area

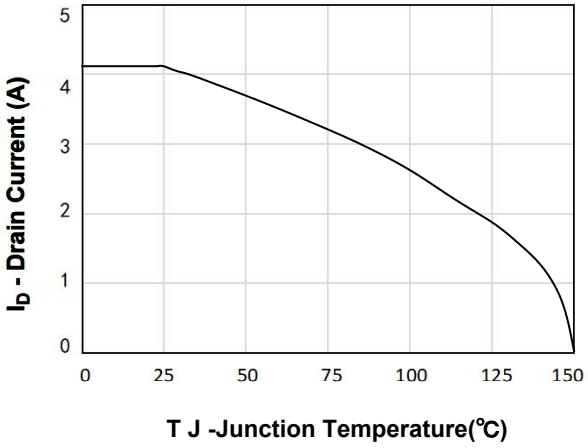


Figure 8. Maximum PContinuous Drain Currentvs Case Temperature

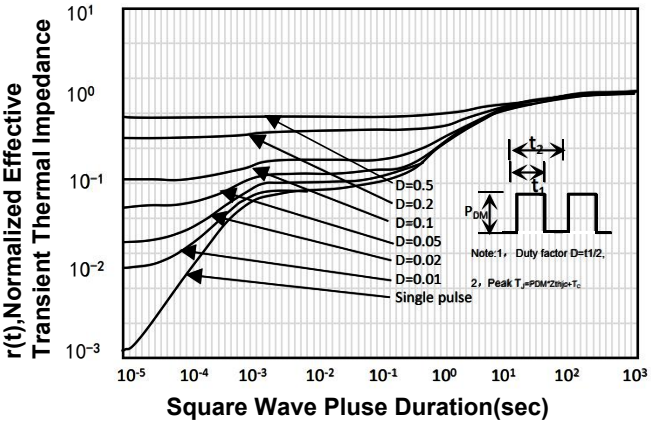
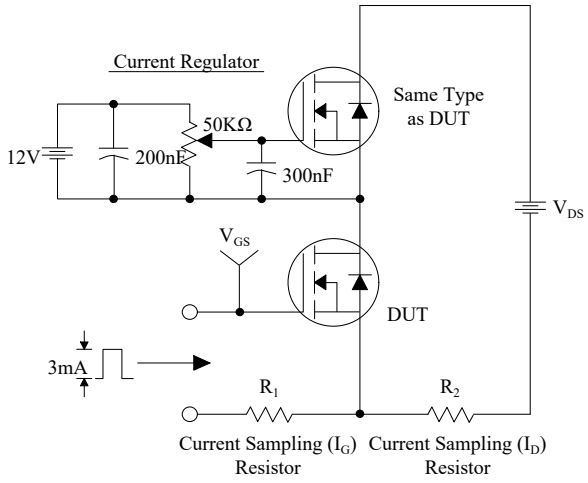
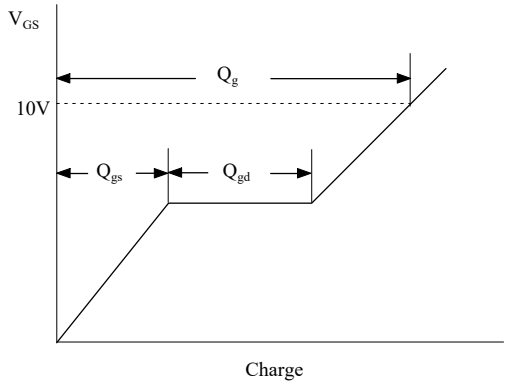


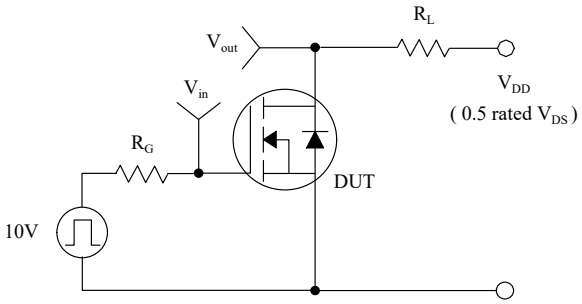
Figure 9. Transient Thermal Response Curve

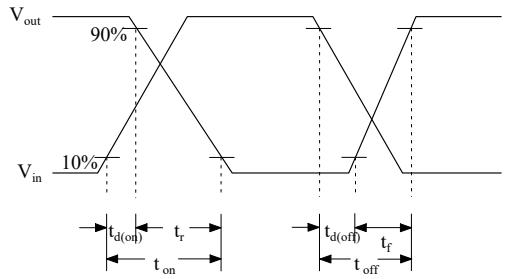
Gate Charge Test Circuit & Waveform



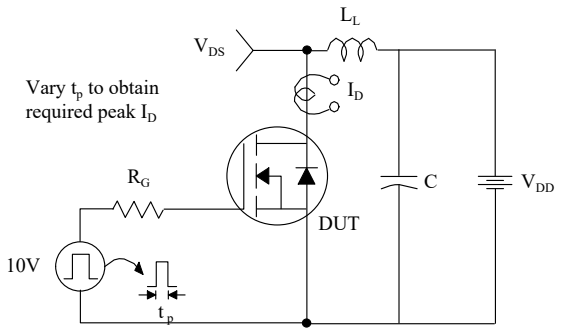


Resistive Switching Test Circuit & Waveforms

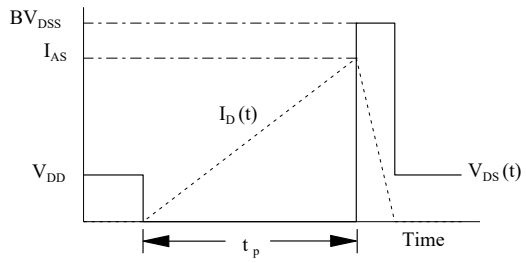




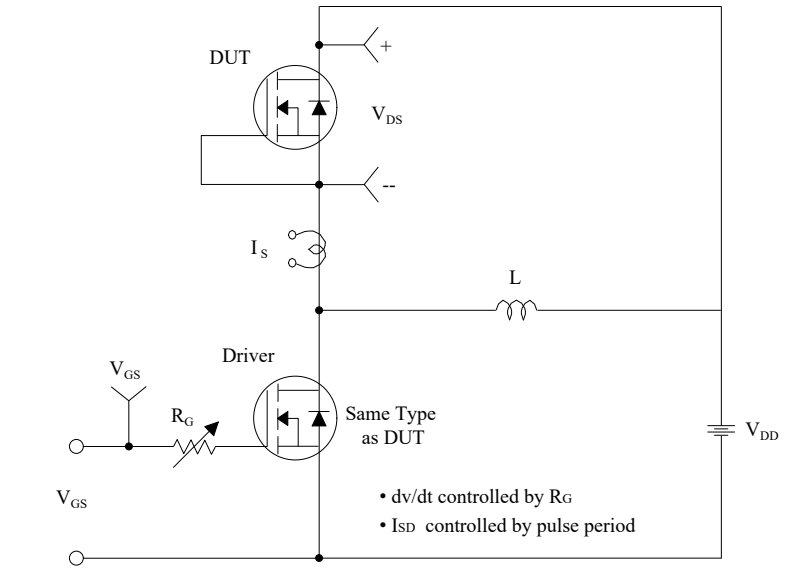
Unclamped Inductive Switching Test Circuit & Waveforms

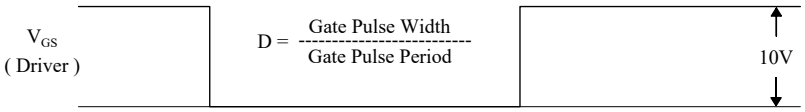


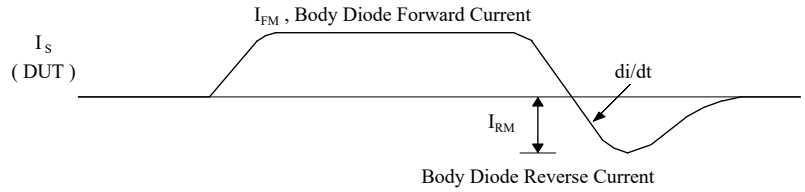
$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$

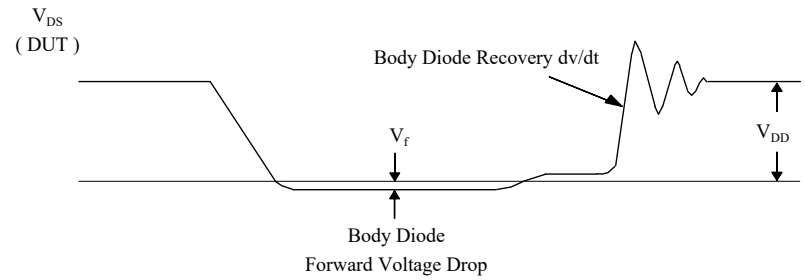


Peak Diode Recovery dv/dt Test Circuit & Waveforms

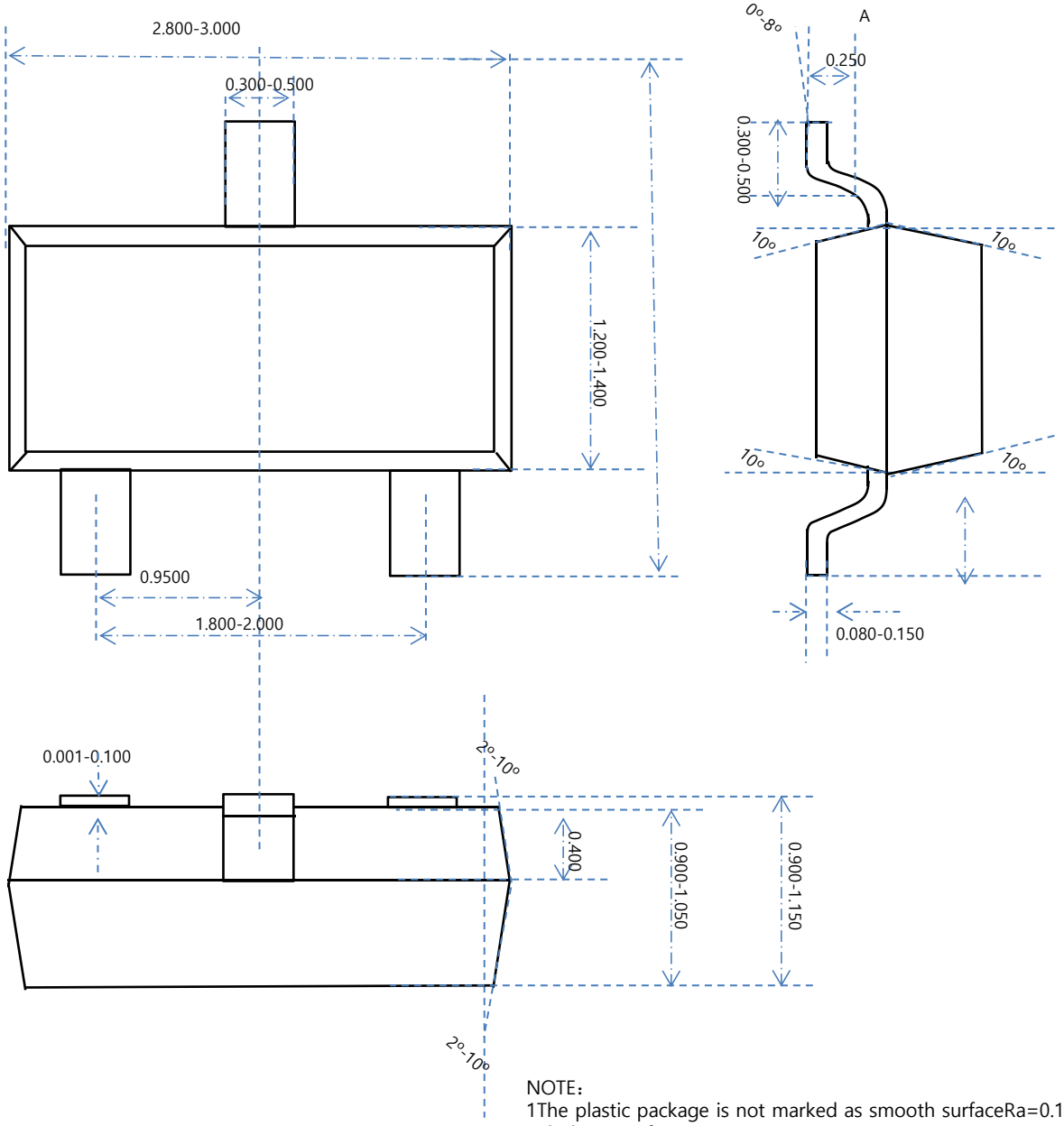








SOT-23 OUTLINE



NOTE：
1The plastic package is not marked as smooth surfaceRa=0.1; Subglossy surfaceRa=0.8
2.Undeclared tolerance±0.25,Unmarked filletRmax=0.25

NAME	SOT-23 OUTLINE	UNIT	mm	DESIGNED	Shawn	THIRD ANGLE SYSTEM
DWGNO		PAGE	1 OF 1	CHECKED		
VERSION	Ver1.0	ISSUE DATE		APPROVED		